

TLP130

Programmable Controllers
 AC / DC-Input Module
 Telecommunication

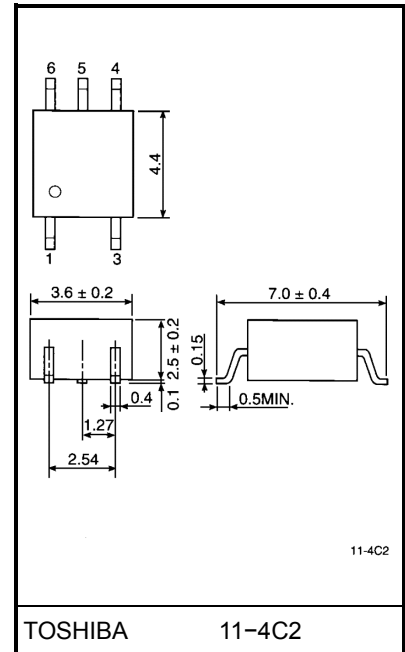
The TOSHIBA mini flat coupler TLP130 is a small outline coupler, suitable for surface mount assembly. TLP130 consists of a photo transistor, optically coupled to two gallium arsenide infrared emitting diode connected inverse parallel, and operate directly by AC input current.

- Collector-emitter voltage: 80V(min.)
- Current transfer ratio: 50%(min.)
 Rank GB: 100%(min.)
- Isolation voltage: 3750Vrms(min.)
- UL recognized: UL1577, file no.E67349
- Current transfer ratio

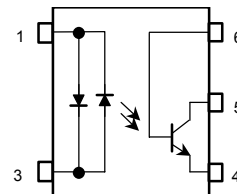
Classi- fication	Current Transfer Ratio		Marking Of Classification
	$I_F = 5\text{mA}, V_{CE} = 5\text{V}, T_a = 25^\circ\text{C}$		
	Min.	Max.	
Standard	50	600	Blank, Y, GR, GB
Rank GB	100	600	GB,GR

(Note) Application type name for certification test, please use standard product type name, i.e. TLP130(GB): TLP130

Unit in mm



Weight: 0.09 g



- 1 : Anode, Cathode
- 3 : Cathode, Anode
- 4 : Emitter
- 5 : Collector
- 6 : Base

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	$I_{F(RMS)}$	50	mA
	Forward current derating (Ta≥53°C)	$\Delta I_F / ^\circ C$	-0.7	mA / °C
	Peak forward current (100μs pulse, 100pps)	I_{FP}	1	A
	Junction temperature	T_j	125	°C
Detector	Collector-emitter voltage	V_{CEO}	80	V
	Collector-base voltage	V_{CBO}	80	V
	Emitter-collector voltage	V_{ECO}	7	V
	Emitter-base voltage	V_{EBO}	7	V
	Collector current	I_C	50	mA
	Peak collector current (10ms pulse, 100pps)	I_{CP}	100	mA
	Power dissipation	P_C	150	mW
	Power dissipation derating (Ta≥25°C)	$\Delta P_C / ^\circ C$	-1.5	mW / °C
	Junction temperature	T_j	125	°C
Storage temperature range		T_{stg}	-55~125	°C
Operating temperature range		T_{opr}	-55~100	°C
Lead soldering temperature (10s)		T_{sol}	260	°C
Total package power dissipation		P_T	200	mW
Total package power dissipation derating (Ta≥25°C)		$\Delta P_T / ^\circ C$	-2.0	mW / °C
Isolation voltage (AC, 1min., RH ≤ 60%) (Note 1)		BV_S	3750	Vrms

(Note 1) Device considered a two terminal device: Pins 1 and 3 shorted together and pins 4, 5 and 6 shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	—	5	48	V
Forward current	$I_{F(RMS)}$	—	16	25	mA
Collector current	I_C	—	1	10	mA
Operating temperature	T_{opr}	-25	—	85	°C

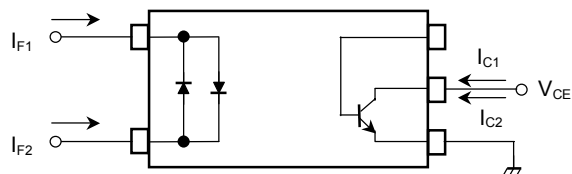
Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V_F	$I_F = \pm 10\text{mA}$	1.0	1.15	1.3	V
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	60	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	80	—	—	V
	Emitter-collector breakdown voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.1\text{mA}$	80	—	—	V
	Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector dark current	I_{CEO}	$V_{CE} = 48\text{V}$	—	10	100	nA
			$V_{CE} = 48\text{V}, T_a = 85^\circ\text{C}$	—	2	50	μA
	Collector dark current	I_{CER}	$V_{CE} = 48\text{V}, T_a = 85^\circ\text{C}$ $R_{BE} = 1\text{M}\Omega$	—	0.5	10	μA
	Collector dark current	I_{CBO}	$V_{CB} = 10\text{V}$	—	0.1	—	nA
	DC forward current gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 0.5\text{mA}$	—	400	—	—
	Capacitance collector to emitter	C_{CE}	$V = 0, f = 1\text{MHz}$	—	10	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I_C / I_F	$I_F = \pm 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_{F(\text{sat})}$	$I_F = \pm 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Base photo-current	I_{PB}	$I_F = \pm 5\text{mA}, V_{CB} = 5\text{V}$	—	10	—	μA
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 2.4\text{mA}, I_F = \pm 8\text{mA}$ $I_C = 0.2\text{mA}, I_F = \pm 1\text{mA}$ Rank GB	—	—	0.4	V
			—	0.2	—	
			—	—	0.4	
Off-state collector current	$I_{C(\text{off})}$	$I_F = \pm 0.7\text{mA}, V_{CE} = 48\text{V}$	—	1	10	μA
CTR symmetry	$I_{C(\text{ratio})}$	$I_C(I_F = -5\text{mA}) / I_C(I_F = 5\text{mA})$ (Note 2)	0.33	—	3	—

(Note 2) $I_{C(\text{ratio})} = \frac{I_{C2}(I_F = I_{F2}, V_{CE} = 5\text{V})}{I_{C1}(I_F = I_{F1}, V_{CE} = 5\text{V})}$



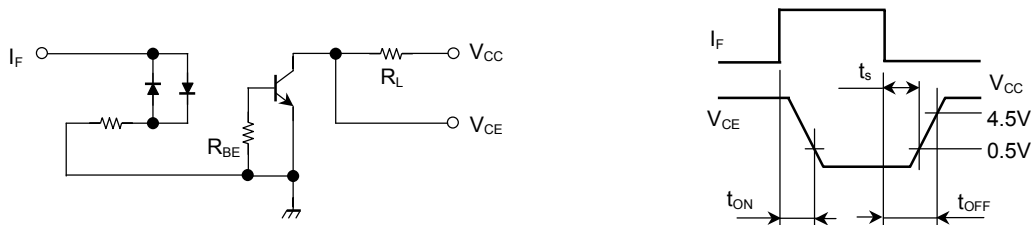
Isolation Characteristics (Ta = 25°C)

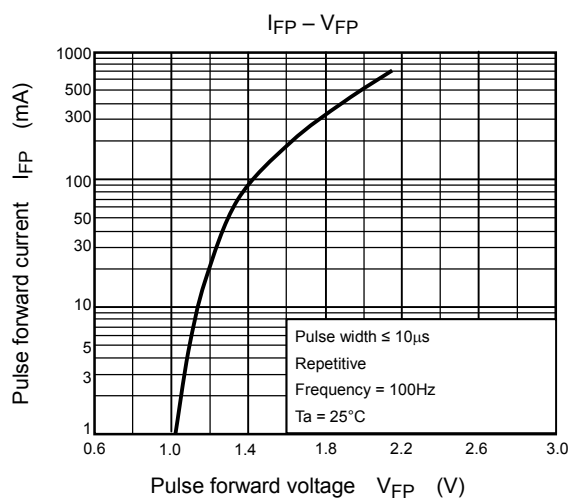
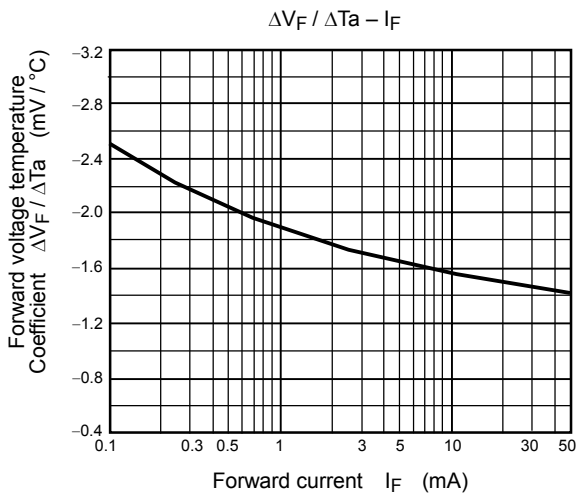
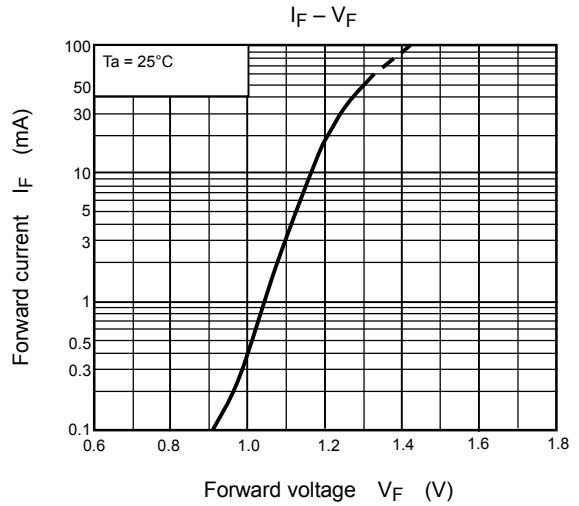
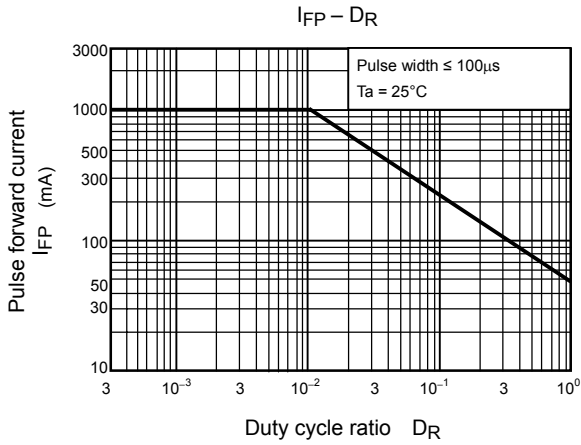
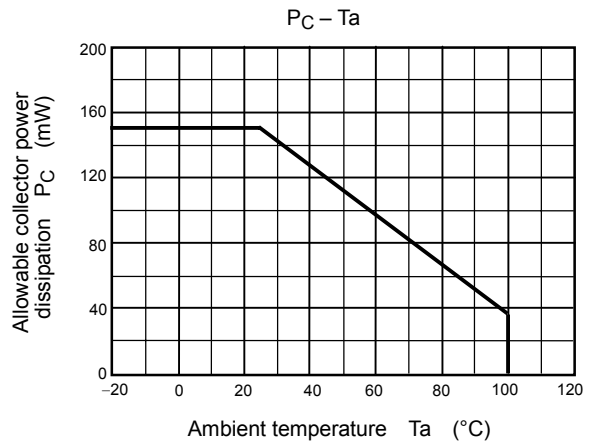
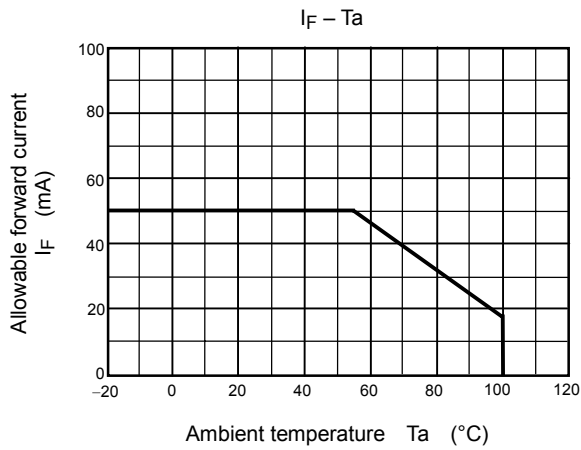
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance input to output	C _S	V _S =0, f=1MHz	—	0.8	—	pF
Isolation resistance	R _S	V _S =500V	5×10 ¹⁰	10 ¹⁴	—	Ω
Isolation voltage	BV _S	AC, 1minute	3750	—	—	V _{rms}
		AC, 1second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V _{dc}

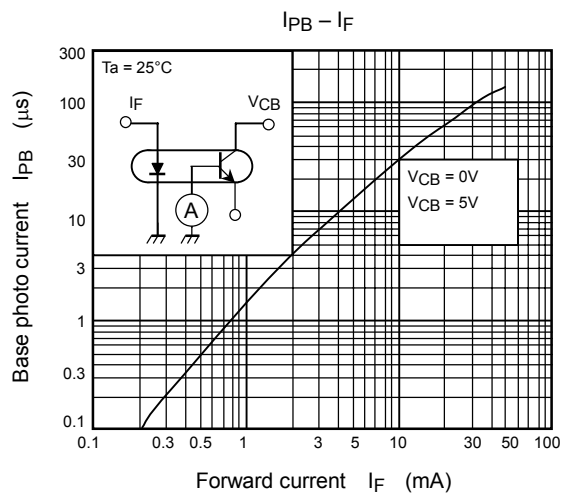
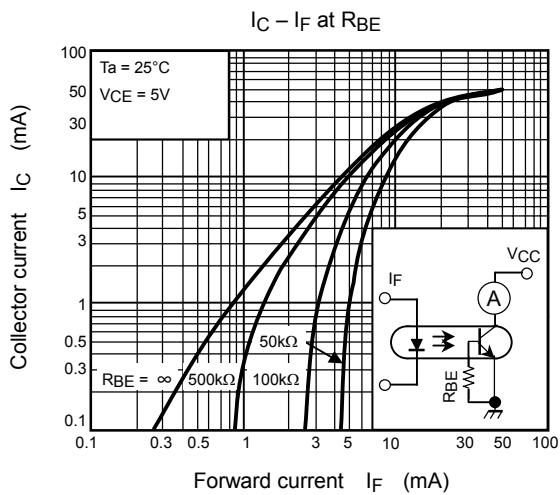
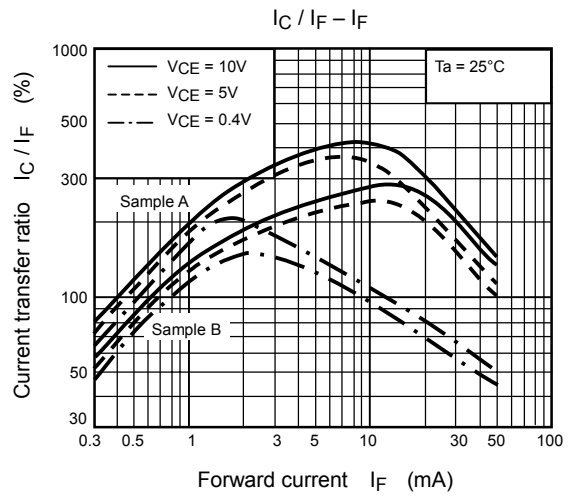
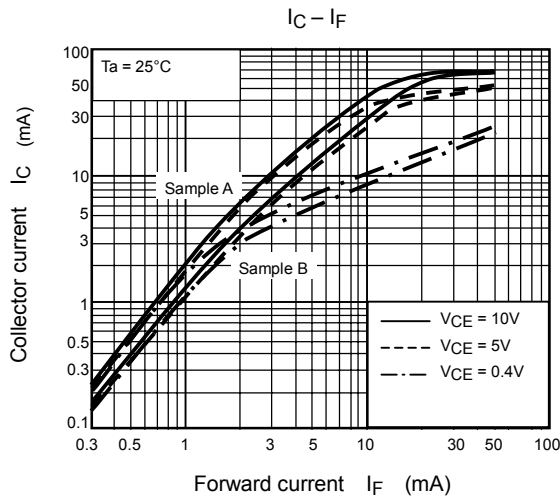
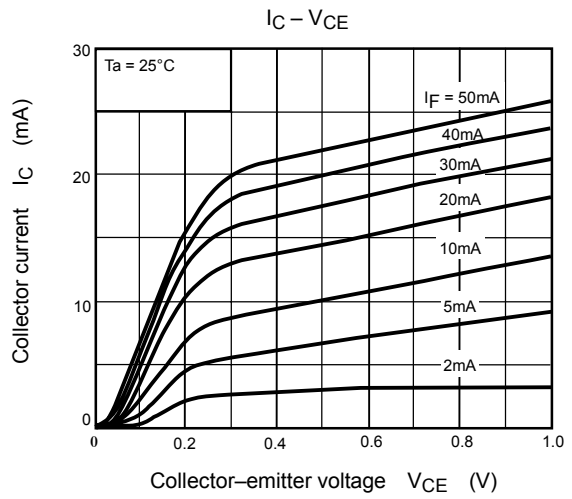
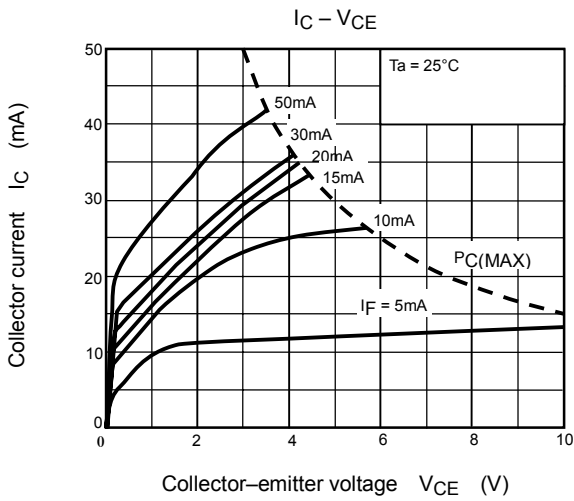
Switching Characteristics (Ta = 25°C)

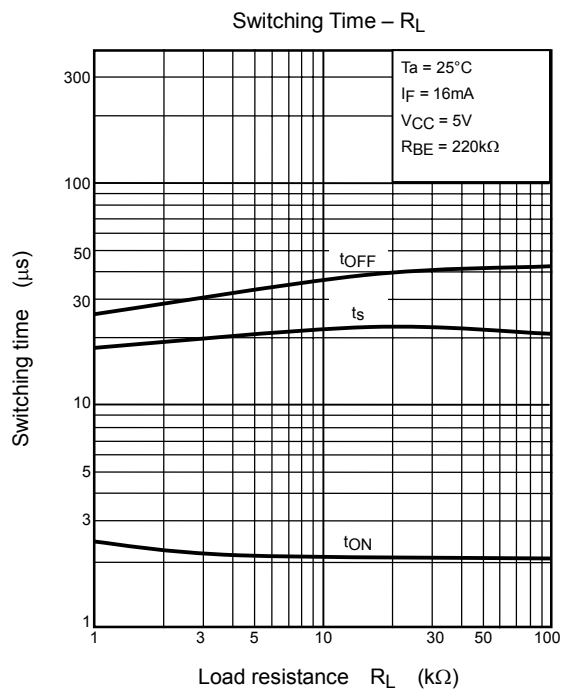
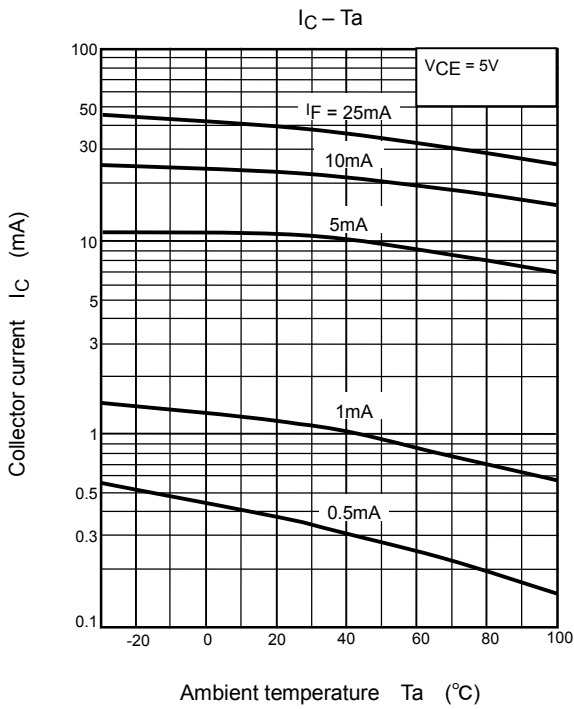
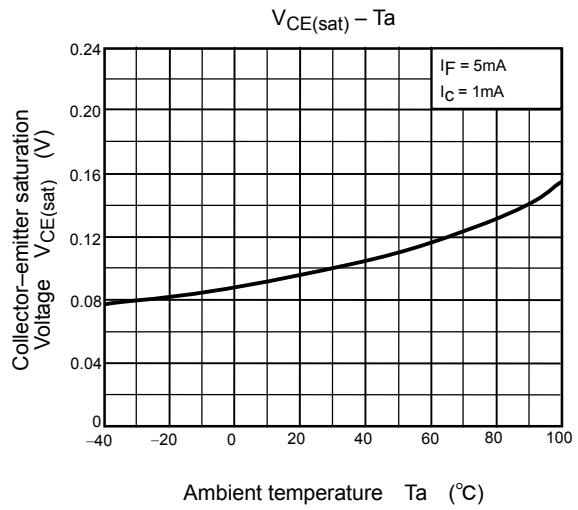
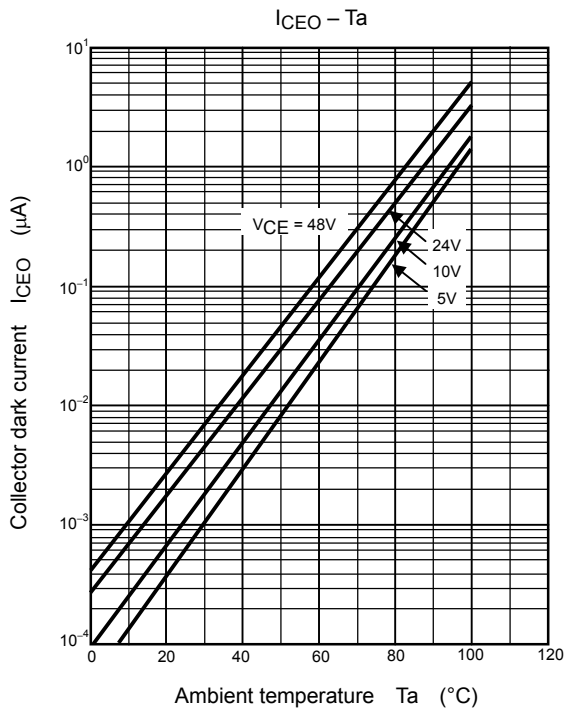
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t _r	V _{CC} = 10V, I _C = 2mA R _L = 100Ω	—	2	—	μs
Fall time	t _f		—	3	—	
Turn-on time	t _{on}		—	3	—	
Turn-off time	t _{off}		—	3	—	
Turn-on time	t _{ON}	R _L = 1.9 kΩ (Fig.1) R _{BE} = OPEN V _{CC} = 5 V, I _F = ±16mA	—	2	—	μs
Storage time	t _S		—	25	—	
Turn-off time	t _{OFF}		—	40	—	
Turn-on time	t _{ON}	R _L = 1.9kΩ (Fig.1) R _{BE} = 220kΩ V _{CC} = 5 V, I _F = ±16mA	—	2	—	μs
Storage time	t _S		—	20	—	
Turn-off time	t _{OFF}		—	30	—	

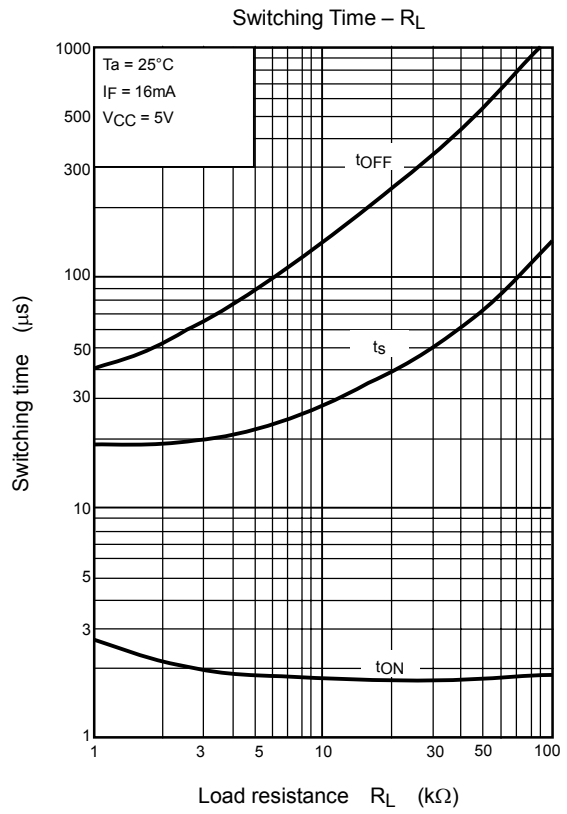
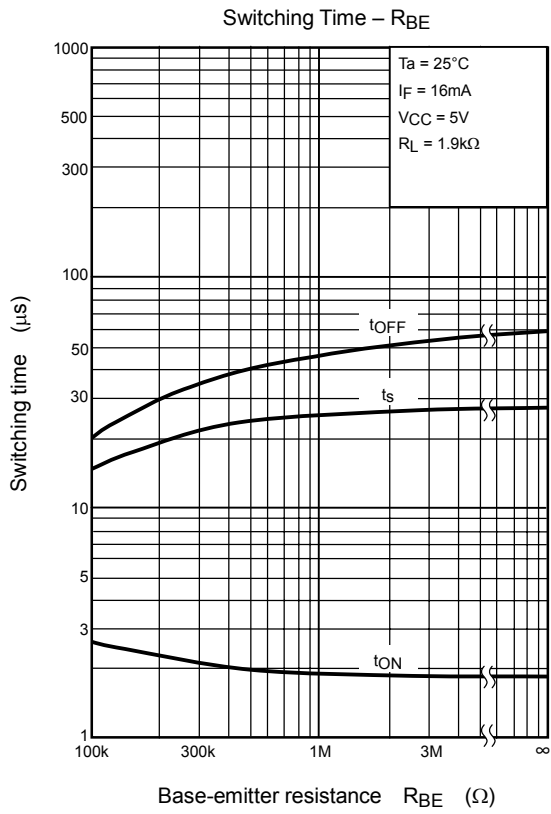
Fig. 1 Switching time test circuit











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